



Complementary Silicon Power Transistors

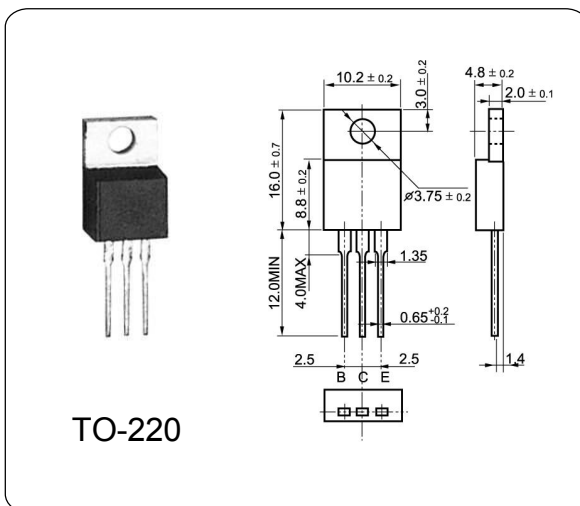
2SB546A / 2SD401A

(Ta = 25 °C)

DESCRIPTION

The 2SB546A and 2SD401A are high voltage triple diffused silicon transistors, These devices are designed for use in line-operated color TV vertical deflection of complementary symmetry circuit,
The 2SB546A and 2SD401A are complementary transistors, consisting of straight leads

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2.0	A
Collector Peak Current	$I_{C(peak)}$	3.0	A
Total Dissipation at	P_{tot}	30	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS SEMICONDUCTOR CO., LTD

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=150V, I_E=0$	—	—	50	uA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=4.0V, I_C=0$	—	—	50	uA
Collector-Emitter Sustaining Voltage	V_{CEO}	$I_C=10mA, I_B=0$	150	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=400mA$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	—	—	2.0	V
Collector capacitance	C_C	$V_{CB}=10V, f=1.0MHz, I_E=0$	—	75/45	—	pF
Transition Frequency	f_T	$V_{CE}=10V, I_C=400mA$	—	7.0	—	MHz